

**60V N-Channel MOSFET**
**1.Product Summary**

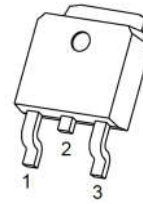
| $V_{(BR)DSS}$ | $R_{DS(on)TYP}$ | $I_D$ |
|---------------|-----------------|-------|
| 60V           | 30mΩ@10V        | 15A   |

**2.Features**

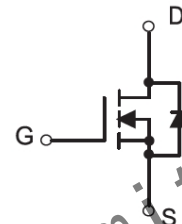
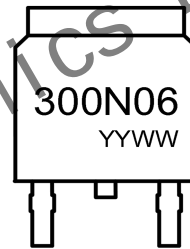
- $V_{DS}$  60V
- $I_D$  15A
- $R_{DS(ON)}$ ( at  $V_{GS}=10V$ ) <40 mohm
- High density cell design for ultra low  $R_{dson}$
- Fully characterized avalanche voltage and current
- Good stability and uniformity with high  $E_{AS}$
- Excellent package for good heat dissipation
- Special process technology for high ESD capability

**3.Applications**

- Power switching application
- Hard switched and high frequency circuits
- Uninterruptible Power Supply

**TO-252**


PIN1:GATE  
PIN2:DRAIN  
PIN3:SOURCE

**Schematic diagram**

**Marking**


300N06 : Device Code  
YY : Year Code  
WW : Week Code

**4.Absolute Maximum rating ( $T_A = 25^{\circ}C$  unless otherwise noted)**

| Parameter                                                |                    | Symbol          | Value      | Unit          |
|----------------------------------------------------------|--------------------|-----------------|------------|---------------|
| Drain-Source Voltage                                     |                    | $V_{DS}$        | 60         | V             |
| Gate-Source Voltage                                      |                    | $V_{GS}$        | $\pm 20$   | V             |
| Continuous Drain Current@10V <sup>1</sup>                | $T_C=25^{\circ}C$  | $I_D$           | 15         | A             |
|                                                          | $T_C=100^{\circ}C$ |                 | 9.5        |               |
|                                                          | $T_A=25^{\circ}C$  |                 | 5          |               |
|                                                          | $T_A=70^{\circ}C$  |                 | 4          |               |
| Pulsed Drain Current <sup>2</sup>                        |                    | $I_{DM}$        | 40         | A             |
| Single Pulse Avalanche Energy <sup>3</sup>               |                    | $E_{AS}$        | 22         | mJ            |
| Avalanche Current                                        |                    | $I_{AS}$        | 21         | A             |
| Total Power Dissipation <sup>4</sup>                     | $T_C=25^{\circ}C$  | $P_D$           | 31.3       | W             |
|                                                          | $T_A=25^{\circ}C$  |                 | 2          |               |
| Thermal Resistance from Junction-to-Ambient <sup>1</sup> |                    | $R_{\theta JA}$ | 62         | $^{\circ}C/W$ |
| Thermal Resistance from Junction-to-Case <sup>1</sup>    |                    | $R_{\theta JC}$ | 4          | $^{\circ}C/W$ |
| Operating Junction and Storage Temperature Range         |                    | $T_J, T_{STG}$  | -55 to+150 | $^{\circ}C$   |

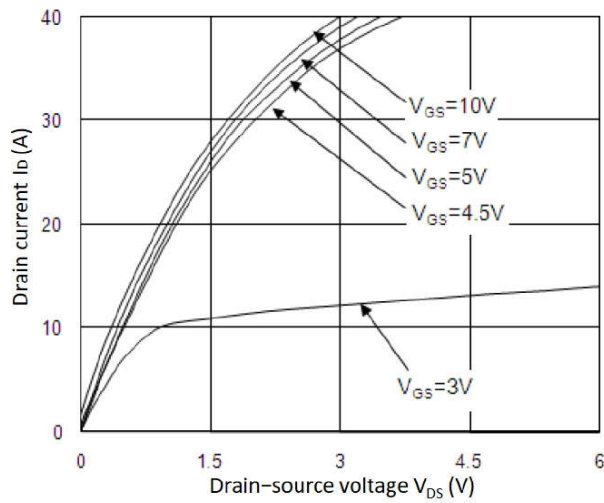
## 5. Electrical Characteristics ( $T_A = 25^\circ\text{C}$ unless otherwise noted)

| Parameter                                | Symbol            | Test Condition                                               | Min | Type | Max       | Unit    |
|------------------------------------------|-------------------|--------------------------------------------------------------|-----|------|-----------|---------|
| Static Characteristics                   |                   |                                                              |     |      |           |         |
| Drain-Source Breakdown Voltage           | $V_{(BR)DSS}$     | $V_{GS} = 0V, I_D = 250\mu A$                                | 60  | -    | -         | V       |
| Gate-body Leakage current                | $I_{GSS}$         | $V_{DS} = 0V, V_{GS} = \pm 20V$                              | -   | -    | $\pm 100$ | nA      |
| Zero Gate Voltage Drain Current          | $T_J=25^{\circ}C$ | $I_{DSS}$<br>$V_{DS} = 60V, V_{GS} = 0V$                     | -   | -    | 1         | $\mu A$ |
|                                          | $T_J=55^{\circ}C$ |                                                              | -   | -    | 5         |         |
| Gate-Threshold Voltage                   | $V_{GS(th)}$      | $V_{DS} = V_{GS}, I_D = 250\mu A$                            | 1.0 | 1.6  | 2.5       | V       |
| Drain-Source On-Resistance <sup>2</sup>  | $R_{DS(on)}$      | $V_{GS} = 10V, I_D = 15A$                                    | -   | 30   | 40        | mΩ      |
|                                          |                   | $V_{GS} = 4.5V, I_D = 7A$                                    | -   | 35   | 50        |         |
| Forward Transconductance                 | $g_{fs}$          | $V_{DS} = 5V, I_D = 15A$                                     | -   | 25.3 | -         | s       |
| Dynamic Characteristics                  |                   |                                                              |     |      |           |         |
| Input Capacitance                        | $C_{iss}$         | $V_{DS} = 15V, V_{GS}=0V, f = 1MHz$                          | -   | 927  | -         | pF      |
| Output Capacitance                       | $C_{oss}$         |                                                              | -   | 62   | -         |         |
| Reverse Transfer Capacitance             | $C_{rss}$         |                                                              | -   | 47   | -         |         |
| Switching Characteristics                |                   |                                                              |     |      |           |         |
| Gate Resistance                          | $R_g$             | $V_{DS} = 0V, V_{GS}= 0V, f = 1MHz$                          | -   | 2.2  | -         | Ω       |
| Total Gate Charge                        | $Q_g$             | $V_{GS} = 10V, V_{DS} = 48V, I_D= 15A$                       | -   | 19   | -         | nC      |
| Gate-Source Charge                       | $Q_{gs}$          |                                                              | -   | 2.5  | -         |         |
| Gate-Drain Charge                        | $Q_{gd}$          |                                                              | -   | 5    | -         |         |
| Turn-On Delay Time                       | $t_{d(on)}$       | $V_{GS} = 10V, V_{DD} = 30V,$<br>$R_G = 3.3\Omega, I_D= 15A$ | -   | 2.8  | -         | ns      |
| Rise Time                                | $t_r$             |                                                              | -   | 16.6 | -         |         |
| Turn-Off Delay Time                      | $t_{d(off)}$      |                                                              | -   | 21.2 | -         |         |
| Fall Time                                | $t_f$             |                                                              | -   | 5.6  | -         |         |
| Drain-Source Body Diode Characteristics  |                   |                                                              |     |      |           |         |
| Diode Forward Voltage <sup>2</sup>       | $V_{SD}$          | $I_S = 1A, V_{GS} = 0V$                                      | -   | -    | 1.2       | V       |
| Continuous Source Current <sup>1,5</sup> | $I_S$             | $V_G=V_D=0V$ , Force Current                                 | -   | -    | 20        | A       |
| Body Diode Reverse Recovery Time         | $t_{rr}$          | $I_F = 15A, d_i/d_t = 100A/\mu s$                            | -   | 12.2 | -         | ns      |
| Body Diode Reverse Recovery Charge       | $Q_{rr}$          |                                                              | -   | 7.3  | -         | nC      |

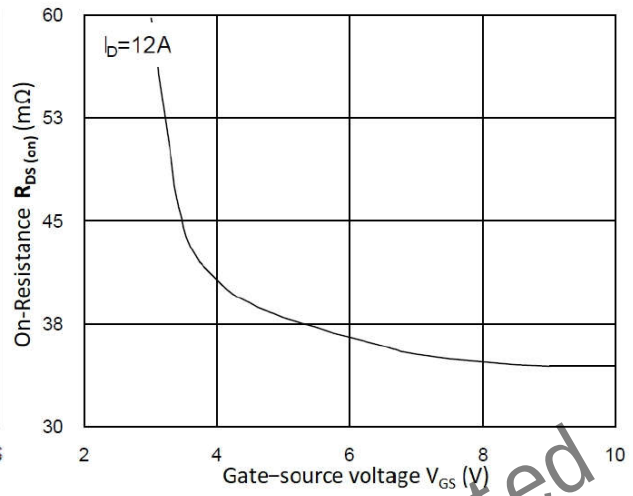
Notes:

1. The data tested by surface mounted on a 1 inch<sup>2</sup> FR-4 board with 20Z copper.
2. The data tested by pulsed , pulse width  $\leq 300\mu s$  , duty cycle  $\leq 2\%$
3. The EAS data shows Max. rating . The test condition is  $V_{DD}=25V, V_{GS}=10V, L=0.1mH, I_{AS}=21A$
4. The power dissipation is limited by  $150^\circ\text{C}$  junction temperature
5. The data is theoretically the same as  $I_D$  and  $I_{DM}$  , in real applications , should be limited by total power dissipation.

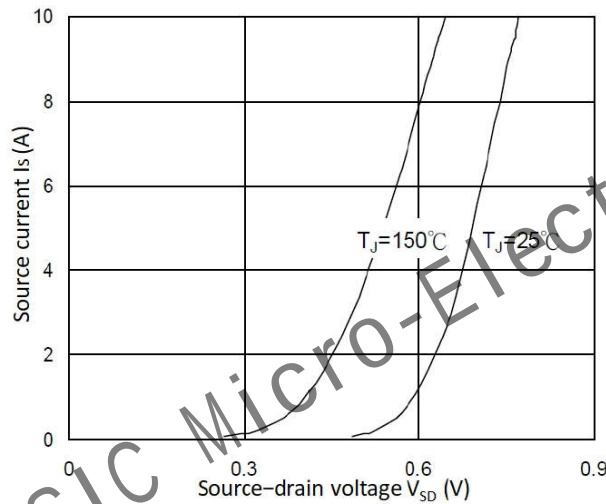
## 6. Typical Characteristic



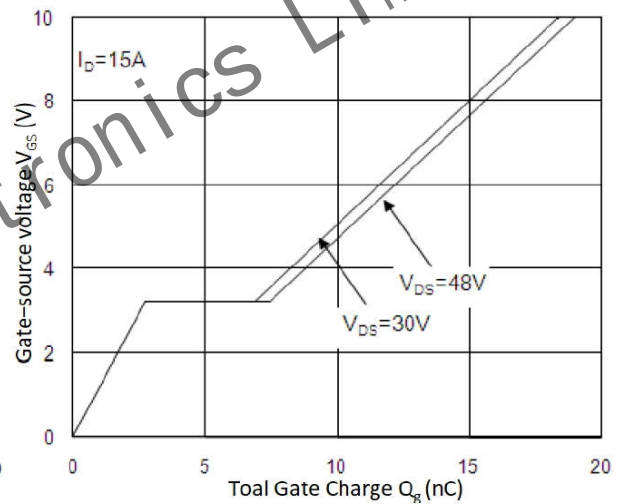
Output Characteristics



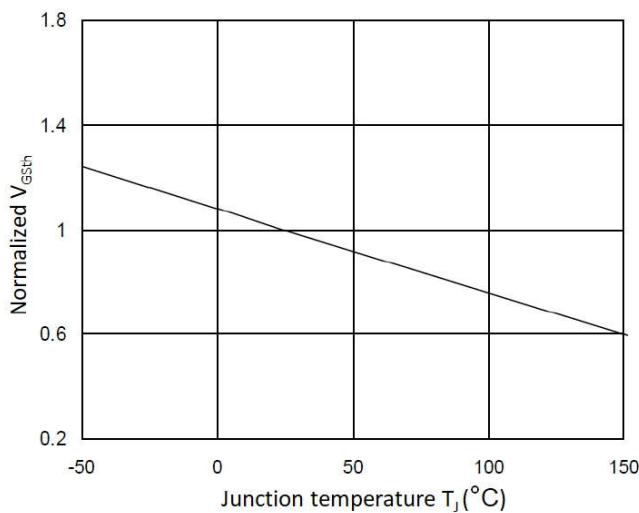
$R_{DS(on)}$  vs.  $V_{GS}$



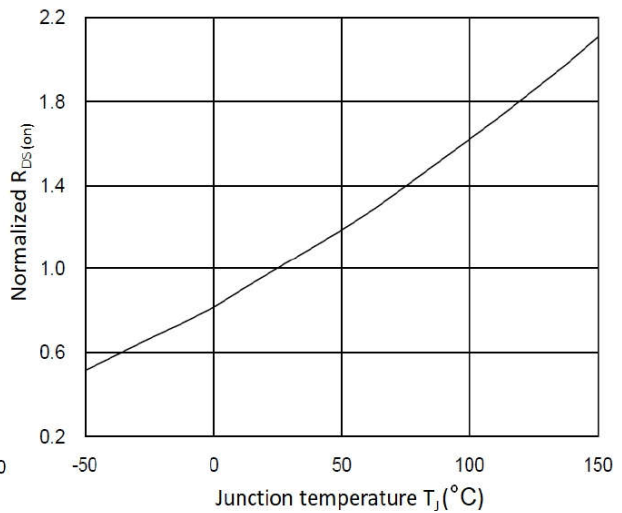
Forward Characteristics of Reverse



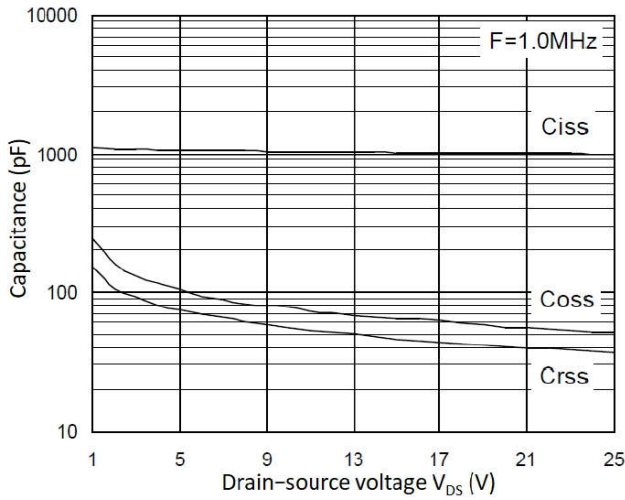
Gate Charge Characteristics



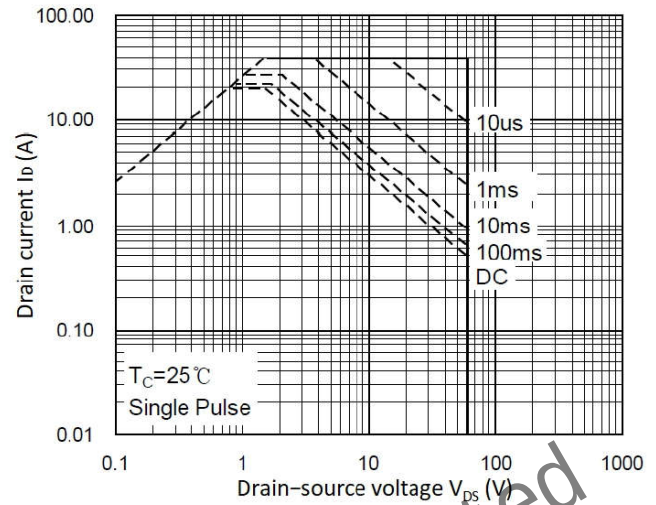
Normalized  $V_{GS(th)}$  vs.  $T_J$



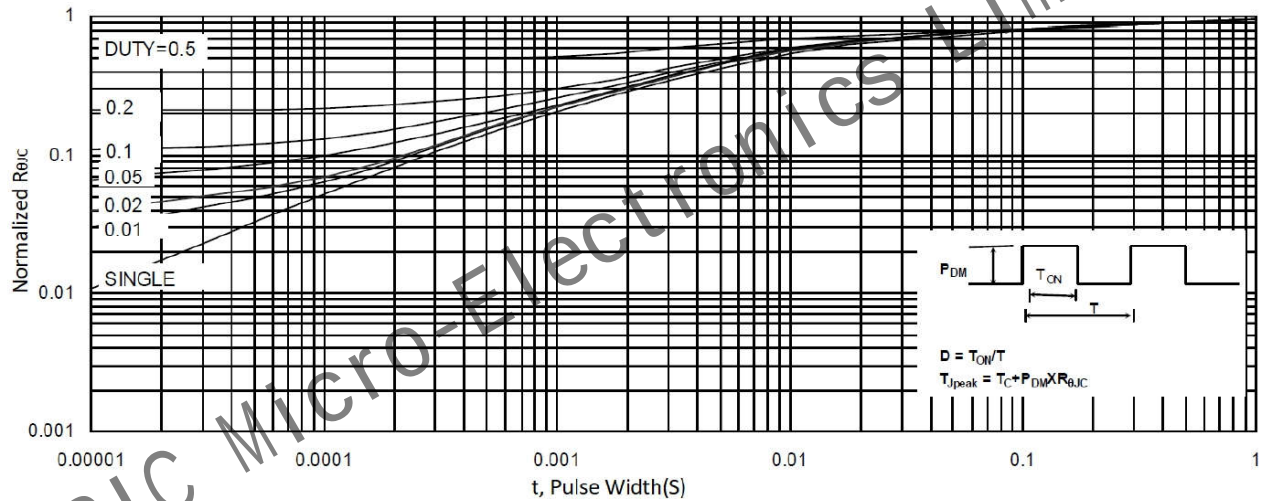
Normalized  $R_{DS(on)}$  vs.  $T_J$



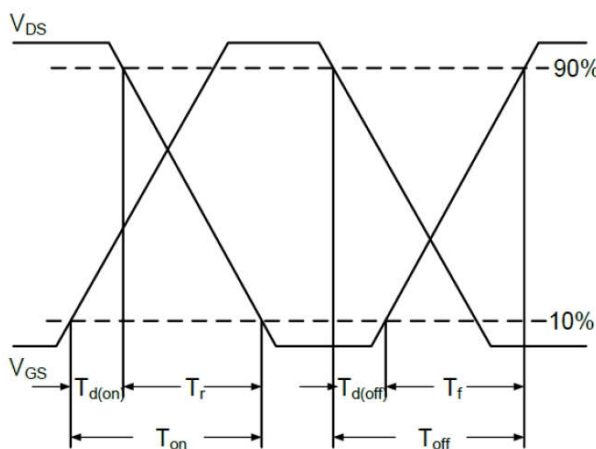
Capacitance Characteristics



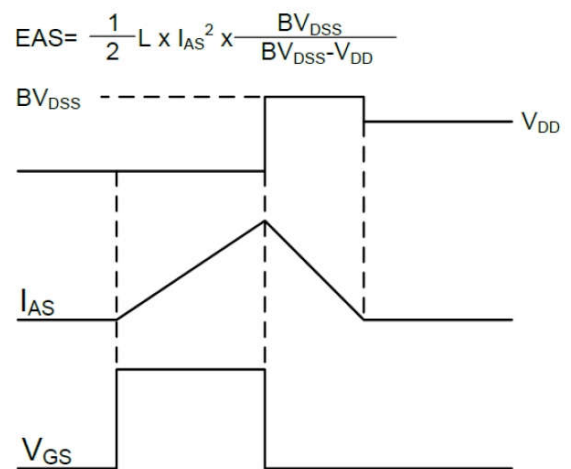
Safe Operating Area



Normalized Maximum Transient Thermal Impedance

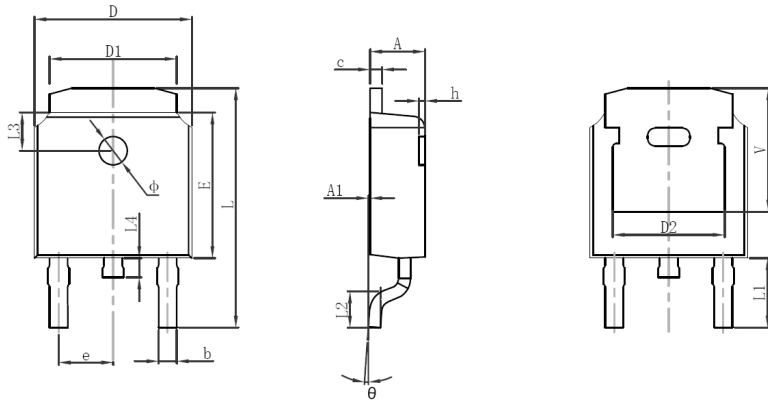


Switching Time Waveform



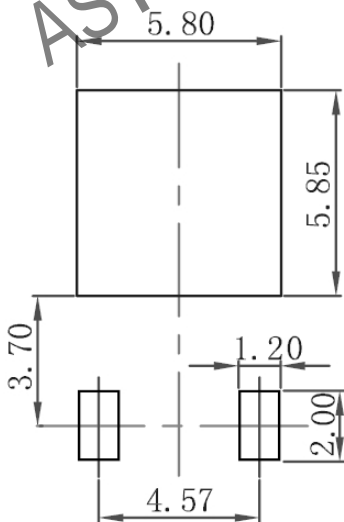
Unclamped Inductive Switching Waveform

## 7.Dimension



| Symbol | Millimeters |        | Inches     |       |
|--------|-------------|--------|------------|-------|
|        | Min         | Max    | Min        | Max   |
| A      | 2.200       | 2.400  | 0.087      | 0.094 |
| A1     | 0.000       | 0.127  | 0.000      | 0.005 |
| b      | 0.635       | 0.770  | 0.025      | 0.030 |
| c      | 0.460       | 0.580  | 0.018      | 0.023 |
| D      | 6.500       | 6.700  | 0.256      | 0.264 |
| D1     | 5.100       | 5.460  | 0.201      | 0.215 |
| D2     | 4.830 REF.  |        | 0.190 REF. |       |
| E      | 6.000       | 6.200  | 0.236      | 0.244 |
| e      | 2.186       | 2.386  | 0.086      | 0.094 |
| L      | 9.712       | 10.312 | 0.382      | 0.406 |
| L1     | 2.900 REF.  |        | 0.114 REF. |       |
| L2     | 1.400       | 1.700  | 0.055      | 0.067 |
| L3     | 1.600 REF.  |        | 0.063 REF. |       |
| L4     | 0.600       | 1.000  | 0.024      | 0.039 |
| Φ      | 1.100       | 1.300  | 0.043      | 0.051 |
| θ      | 0°          | 8°     | 0°         | 8°    |
| h      | 0.000       | 0.300  | 0.000      | 0.012 |
| V      | 5.250 REF.  |        | 0.207 REF. |       |

## 8.Recommended Land Pattern

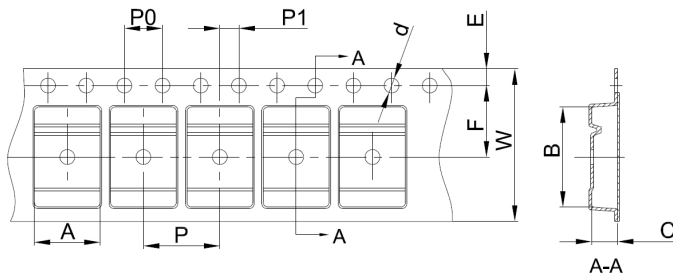


### Note:

1. Controlling dimension: in millimeters
2. General tolerance:  $\pm 0.05\text{mm}$
3. The pad layout is for reference only
4. Unit: mm

## 9.Tape and Reel

### TO-252-2L Embossed Carrier Tape

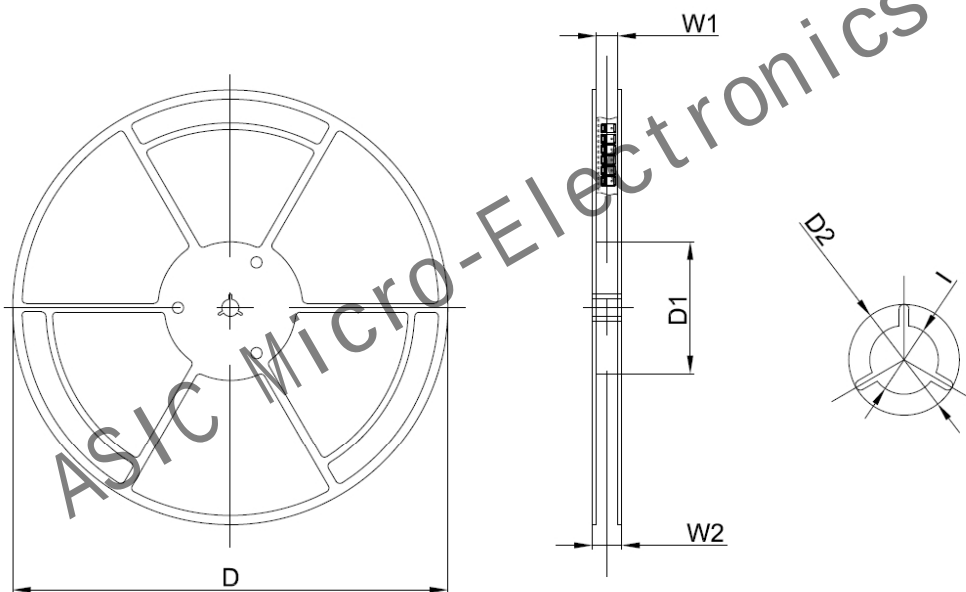


#### Packaging Description:

TO-252 parts are shipped in tape. The carrier tape is made from a dissipative (carbon filled) polycarbonate resin. The cover tape is a multilayer film (Heat Activated Adhesive in nature) primarily composed of polyester film, adhesive layer, sealant, and anti-static sprayed agent. These reeled parts in standard option are shipped with 25,00 units per 13" or 33.0 cm diameter reel. The reels are clear in color and is made of polystyrene plastic (anti-static coated).

| Dimensions are in millimeter |      |       |      |       |      |      |      |      |      |       |
|------------------------------|------|-------|------|-------|------|------|------|------|------|-------|
| Pkg type                     | A    | B     | C    | d     | E    | F    | P0   | P    | P1   | W     |
| TO-252                       | 6.90 | 10.50 | 2.70 | Ø1.55 | 1.75 | 7.50 | 4.00 | 8.00 | 2.00 | 16.00 |

### TO-252-2L Reel



| Dimensions are in millimeter |        |        |        |       |       |        |
|------------------------------|--------|--------|--------|-------|-------|--------|
| Reel Option                  | D      | D1     | D2     | W1    | W2    | I      |
| 13"Dia                       | 330.00 | 100.00 | Ø21.00 | 16.40 | 21.00 | Ø13.00 |

| REEL      | Reel Size | Box       | Box Size(mm) | Carton     | Carton Size(mm) | G.W.(kg) |
|-----------|-----------|-----------|--------------|------------|-----------------|----------|
| 2,500 pcs | 13inch    | 2,500 pcs | 340×336×29   | 25,000 pcs | 353×346×365     |          |

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